

CDCE913-Q1 和 CDCEL913-Q1 具有 1.8V、2.5V 和 3.3V 输出的可编程 1-PLL VCXO 时钟合成器

1 特性

- 符合汽车应用要求
- 具有符合 AEC-Q100 标准的下列特性：
 - 器件温度等级
 - CDCE913-Q1 1 级：-40°C 至 +125°C 环境温度工作温度范围
 - CDCEL913-Q1 3 级：-40°C 至 +85°C 环境温度工作温度范围
 - 器件 HBM ESD 分类等级 H2
 - 器件 CDM ESD 分类等级 C6
- 功能安全型
 - 可帮助进行功能安全系统设计的文档
- 系统内可编程和 EEPROM
 - 串行可编程易失性寄存器
 - 用于存储客户设置的非易失性 EEPROM
- 灵活的输入计时理念
 - 外部晶体：8MHz 至 32MHz
 - 片上 VCXO：拉动范围 ± 150 ppm
 - 高达 160MHz 的单端 LVCMOS
- 高达 230MHz 的自由可选输出频率
- 低噪声 PLL 内核
 - 已集成的 PLL 环路滤波器组件
 - 低电平周期抖动（典型值 50ps）
- 独立的输出电源引脚：
 - CDCE913-Q1：3.3V 和 2.5V
 - CDCEL913-Q1：1.8V
- 灵活的时钟驱动器
 - 三个用户可定义的控制输入 [S0、S1、S2]，例如 SSC 选择、频率切换、输出使能或断电
 - 为视频、音频、USB、IEEE1394、RFID、Bluetooth®、WLAN、Ethernet 和 GPS 生成高精度时钟
 - 生成适用于 TI DaVinci™、OMAP™ 和 DSP 的常见时钟频率
 - 可编程 SSC 调制
 - 启用 0-PPM 时钟生成功能
- 1.8V 器件电源
- 采用 TSSOP 封装
- 适用于简易 PLL 设计和编程的开发和编程套件 (TI Pro-Clock™)

2 应用

- 仪表组
- 音响主机
- 导航系统
- 高级驾驶辅助系统 (ADAS)

3 说明

CDCE913-Q1 和 CDCEL913-Q1 器件是基于模块化锁相环 (PLL) 的可编程时钟合成器。这些器件提供了灵活的可编程选项，例如输出时钟、输入信号和控制引脚，方便用户针对具体规格需求配置 CDCE913-Q1 和 CDCEL913-Q1。

CDCE913-Q1 和 CDCEL913-Q1 可基于单一输入频率生成多达三种输出时钟，节省电路板空间的同时降低成本。此外，凭借多个输出，时钟发生器可以使用一个发生器来替代多个晶振。这使得该器件非常适合信息娱乐系统中的音响主机和远程信息处理应用，以及 ADAS 系统中的摄像头应用，因为这些平台正在向更小、更具成本效益的系统发展。

此外，借助集成的可配置 PLL，可在系统内针对任何时钟频率（最高可达 230MHz）对每个输出进行编程。PLL 还支持具有可编程向下扩频和中心扩频功能的可编程扩频时钟 (SSC)。这为客户的产品提供了更好的抗电磁干扰 (EMI) 性能，确保通过 CISPR-25 等行业标准。

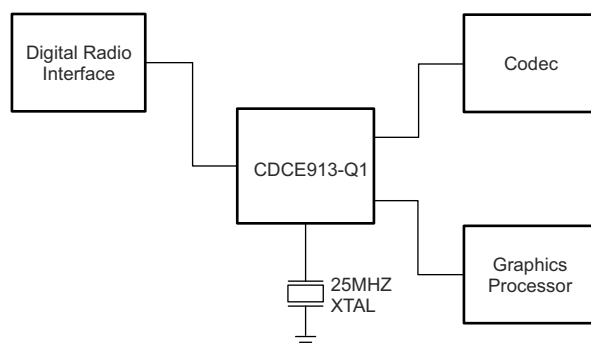
使用三个用户自定义控制引脚可定制频率编程和 SSC。这样就无需使用额外的接口来控制时钟。此外，具体的上电和掉电序列可根据用户需求定义。

封装信息

器件型号	封装 ⁽¹⁾	封装尺寸 ⁽²⁾
CDCE913-Q1	PW (TSSOP, 14)	5mm x 6.4mm
CDCEL913-Q1		

- 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。
- 封装尺寸（长 × 宽）为标称值，并包括引脚（如适用）。





简化原理图

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4 Device Comparison

表 4-1. Device Comparison

DEVICE	SUPPLY (V)	PLL	OUTPUT
CDCE913-Q1	2.5 to 3.3	1	3
CDCEL913-Q1	1.8	1	3
CDCE937-Q1	2.5 to 3.3	3	7
CDCEL937-Q1	1.8	3	7
CDCE949-Q1	2.5 to 3.3	4	9
CDCEL949-Q1	1.8	4	9

5 Pin Configuration and Functions

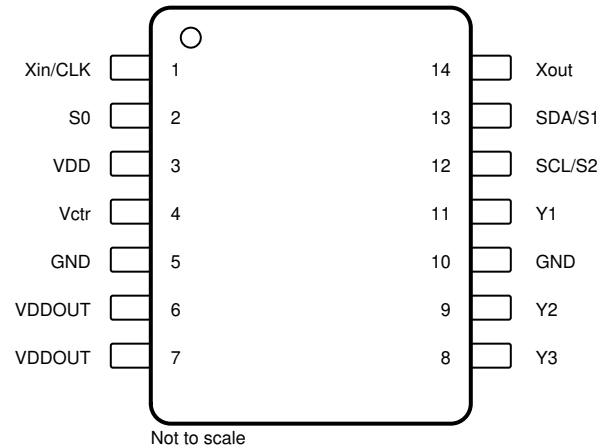


图 5-1. PW Package 14-Pin TSSOP Top View

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
GND	5, 10	G	Ground
SCL/S2	12	I	SCL: serial clock input LVCMOS (default configuration), 500-k Ω internal pullup; or S2: user-programmable control input, LVCMOS input, 500-k Ω internal pullup
SDA/S1	13	I/O or I	SDA: bidirectional serial data input/output (default configuration), LVCMOS internal pullup; or S1: user-programmable control input, LVCMOS input, 500-k Ω internal pullup
S0	2	I	User-programmable control input S0, LVCMOS input, 500-k Ω internal pullup
V _{ctr}	4	I	VCXO control voltage (leave open or pull up when not used)
V _{DD}	3	P	1.8-V power supply for the device
V _{DDOUT}	6, 7	P	CDCE913-Q1: 3.3-V or 2.5-V supply for all outputs
			CDCEL913-Q1: 1.8-V supply for all outputs
Xin/CLK	1	I	Crystal oscillator input or LVCMOS clock input (selectable through the I ² C bus)
Xout	14	O	Crystal oscillator output (leave open or pull up when not used)
Y1	11	O	LVCMOS output
Y2	9	O	LVCMOS output
Y3	8	O	LVCMOS output

(1) G = Ground, I = Input, O = Output, P = Power

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{DD}	Supply voltage		– 0.5	2.5	V
V _{DDOUT}	Output clocks supply voltage	CDCE913-Q1	– 0.5	V _{DD}	V
		CDCEL913-Q1	– 0.5	3.6 + 0.5	
V _I	Input voltage ^{(2) (3)}		– 0.5	V _{DD} + 0.5	V
V _O	Output voltage ⁽²⁾		– 0.5	V _{DDOUT} + 0.5	V
I _I	Input current (V _I < 0, V _I > V _{DD})			20	mA
I _O	Continuous output current			50	mA
T _J	Maximum junction temperature			125	°C
T _{stg}	Storage temperature		– 65	150	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output negative voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (3) SDA and SCL can go up to 3.6 V, as stated in the *Recommended Operating Conditions* table.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per AEC Q100-011 ⁽²⁾	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.
- (2) Charged-device model ESD rating for corner pins is 750 V.

6.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V _{DD}	Device supply voltage		1.7	1.8	1.9	V
V _O	Output Yx supply voltage, V _{DDOUT}	CDCE913-Q1	2.3		3.6	V
		CDCEL913-Q1	1.7		1.9	
V _{IL}	Low-level input voltage, LVCMOS				0.3 × V _{DD}	V
V _{IH}	High-level input voltage, LVCMOS		0.7 × V _{DD}			V
V _{I(thresh)}	Input voltage threshold, LVCMOS			0.5 × V _{DD}		V
V _{I(S)}	Input voltage	S0	0		1.9	V
		S1, S2, SDA, SCL (V _{I(thresh)} = 0.5 V _{DD})	0		3.6	
V _{I(CLK)}	Input voltage range CLK		0		1.9	V
I _{OH} , I _{OL}	Output current	V _{DDOUT} = 3.3 V			±12	mA
		V _{DDOUT} = 2.5 V			±10	
		V _{DDOUT} = 1.8 V			±8	
C _L	Output load, LVCMOS				15	pF
T _A	Operating ambient temperature	CDCE913-Q1	– 40		125	°C
		CDCEL913-Q1	– 40		85	

		MIN	NOM	MAX	UNIT
CRYSTAL AND VCXO SPECIFICATIONS ⁽¹⁾					
f_{Xtal}	Crystal input frequency (fundamental mode)	8	27	32	MHz
ESR	Effective series resistance			100	Ω
f_{PR}	Pulling range ($0 \text{ V} \leq V_{\text{ctr}} \leq 1.8 \text{ V}$) ⁽²⁾	± 120	± 150		ppm
V_{ctr}	Frequency control voltage	0		V_{DD}	V
C_0 / C_1	Pullability ratio			220	
C_L	On-chip load capacitance at Xin and Xout	0		20	pF

- (1) For more information about VCXO configuration and crystal recommendation, see [VCXO Application Guideline for CDCE\(L\)9xx Family \(SCAA085\)](#).
- (2) Pulling range depends on crystal type, on-chip crystal load capacitance, and PCB stray capacitance; pulling range of minimum ± 120 ppm applies for crystal listed in [VCXO Application Guideline for CDCE\(L\)9xx Family \(SCAA085\)](#).

6.4 Thermal Information

THERMAL METRIC ^{(1) (2)}		CDCE913-Q1, CDCEL913-Q1	UNIT
		PW (TSSOP)	
		14 PINS	
$R_{\theta \text{ JA}}$	Junction-to-ambient thermal resistance	110.6	$^{\circ}\text{C/W}$
$R_{\theta \text{ JC(top)}}$	Junction-to-case (top) thermal resistance	35.4	$^{\circ}\text{C/W}$
$R_{\theta \text{ JB}}$	Junction-to-board thermal resistance	53.6	$^{\circ}\text{C/W}$
ψ_{JT}	Junction-to-top characterization parameter	2.1	$^{\circ}\text{C/W}$
ψ_{JB}	Junction-to-board characterization parameter	52.8	$^{\circ}\text{C/W}$
$R_{\theta \text{ JC(bot)}}$	Junction-to-case (bottom) thermal resistance	—	$^{\circ}\text{C/W}$

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report (SPRA953).
- (2) The package thermal impedance is calculated in accordance with JESD 51 and JEDEC2S2P (high-K board).

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

		TEST CONDITIONS		MIN	TYP ⁽¹⁾	MAX	UNIT
OVERALL PARAMETER							
I _{DD}	Supply current (see 图 6-1)	All outputs off, f _{CLK} = 27 MHz, f _{VCO} = 135 MHz, f _{OUT} = 27 MHz	All PLLS on	11		mA	
			Per PLL	9			
I _{DD(OUT)}	Supply current (see 图 6-2 and 图 6-3)	No load, all outputs on, f _{OUT} = 27 MHz	V _{DDOUT} = 3.3 V	1.3		mA	
			V _{DDOUT} = 1.8 V	0.7			
I _{DD(PD)}	Power-down current. Every circuit powered down except I ² C	f _{IN} = 0 MHz, V _{DD} = 1.9 V		30		μA	
V _(PUC)	Supply voltage V _{DD} threshold for power-up control circuit			0.85		1.45	V
f _{VCO}	VCO frequency range of PLL			80		230	MHz
f _{OUT}	LVCMOS output frequency	V _{DDOUT} = 3.3 V				230	MHz
		V _{DDOUT} = 1.8 V				230	
LVCMOS PARAMETER							
V _{IK}	LVCMOS input voltage	V _{DD} = 1.7 V, I _I = - 18 mA				- 1.2	V
I _I	LVCMOS input current	V _I = 0 V or V _{DD} , V _{DD} = 1.9 V				±5	μA
I _{IH}	LVCMOS input current for S0, S1, and S2	V _I = V _{DD} , V _{DD} = 1.9 V				5	μA
I _{IL}	LVCMOS input current for S0, S1, and S2	V _I = 0 V, V _{DD} = 1.9 V				- 4	μA

over recommended operating free-air temperature range (unless otherwise noted)

		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
C _I	Input capacitance at Xin/CLK	V _{IClk} = 0 V or V _{DD}		6		pF
	Input capacitance at Xout	V _{IXout} = 0 V or V _{DD}		2		
	Input capacitance at S0, S1, and S2	V _{IS} = 0 V or V _{DD}		3		
CDCE913-Q1, LVCMOS PARAMETER FOR V _{DDOUT} = 3.3-V MODE						
V _{OH}	LVCMOS high-level output voltage	V _{DDOUT} = 3 V, I _{OH} = - 0.1 mA		2.9		V
		V _{DDOUT} = 3 V, I _{OH} = - 8 mA		2.4		
		V _{DDOUT} = 3 V, I _{OH} = - 12 mA		2.2		
V _{OL}	LVCMOS low-level output voltage	V _{DDOUT} = 3 V, I _{OL} = 0.1 mA			0.1	V
		V _{DDOUT} = 3 V, I _{OL} = 8 mA			0.5	
		V _{DDOUT} = 3 V, I _{OL} = 12 mA			0.8	
t _{PLH} , t _{PHL}	Propagation delay	PLL bypass		3.2		ns
t _r , t _f	Rise and fall time	V _{DDOUT} = 3.3 V (20% - 80%)		0.6		ns
t _{jlt(cc)}	Cycle-to-cycle jitter for Y1 to Y3 ^{(2) (3)}	1 PLL switching, Y2-to-Y3, 10,000 cycles		50	200	ps
t _{jlt(per)}	Peak-to-peak period jitter for Y1 to Y3 ^{(2) (3)}	1 PLL switching, Y2-to-Y3		60	200	ps
t _{sk(o)}	Output skew (see 表 8-2) ⁽⁴⁾	f _{OUT} = 50 MHz, Y1-to-Y3			440	ps
odc	Output duty cycle ⁽⁵⁾	f _{VCO} = 100 MHz, Pdiv = 1		45%	55%	
CDCE913-Q1, LVCMOS PARAMETER FOR V _{DDOUT} = 2.5-V MODE						
V _{OH}	LVCMOS high-level output voltage	V _{DDOUT} = 2.3 V, I _{OH} = - 0.1 mA		2.2		V
		V _{DDOUT} = 2.3 V, I _{OH} = - 6 mA		1.7		
		V _{DDOUT} = 2.3 V, I _{OH} = - 10 mA		1.6		
V _{OL}	LVCMOS low-level output voltage	V _{DDOUT} = 2.3 V, I _{OL} = 0.1 mA			0.1	V
		V _{DDOUT} = 2.3 V, I _{OL} = 6 mA			0.5	
		V _{DDOUT} = 2.3 V, I _{OL} = 10 mA			0.7	
t _{PLH} , t _{PHL}	Propagation delay	PLL bypass		3.6		ns
t _r , t _f	Rise and fall time	V _{DDOUT} = 2.5 V (20% - 80%)		0.8		ns
t _{jlt(cc)}	Cycle-to-cycle jitter for Y1 to Y3 ^{(2) (3)}	1 PLL switching, Y2-to-Y3, 10,000 cycles		50	200	ps
t _{jlt(per)}	Peak-to-peak period jitter for Y1 to Y3 ^{(2) (3)}	1 PLL switching, Y2-to-Y3		60	200	ps
t _{sk(o)}	Output skew (see 表 8-2) ⁽⁴⁾	f _{OUT} = 50 MHz, Y1-to-Y3			440	ps
odc	Output duty cycle ⁽⁵⁾	f _{VCO} = 100 MHz, Pdiv = 1		45%	55%	
CDCEL913-Q1, LVCMOS PARAMETER FOR V _{DDOUT} = 1.8-V MODE						
V _{OH}	LVCMOS high-level output voltage	V _{DDOUT} = 1.7 V, I _{OH} = - 0.1 mA		1.6		V
		V _{DDOUT} = 1.7 V, I _{OH} = - 4 mA		1.4		
		V _{DDOUT} = 1.7 V, I _{OH} = - 8 mA		1.1		
V _{OL}	LVCMOS low-level output voltage	V _{DDOUT} = 1.7 V, I _{OL} = 0.1 mA			0.1	V
		V _{DDOUT} = 1.7 V, I _{OL} = 4 mA			0.3	
		V _{DDOUT} = 1.7 V, I _{OL} = 8 mA			0.6	
t _{PLH} , t _{PHL}	Propagation delay	PLL bypass		2.6		ns
t _r , t _f	Rise and fall time	V _{DDOUT} = 1.8 V (20% - 80%)		0.7		ns
t _{jlt(cc)}	Cycle-to-cycle jitter for Y1 to Y3 ^{(2) (3)}	1 PLL switching, Y2-to-Y3, 10,000 cycles		80	110	ps
t _{jlt(per)}	Peak-to-peak period jitter for Y1 to Y3 ^{(2) (3)}	1 PLL switching, Y2-to-Y3		100	130	ps
t _{sk(o)}	Output skew (see 表 8-2) ⁽⁴⁾	f _{OUT} = 50 MHz, Y1-to-Y3			50	ps
odc	Output duty cycle ⁽⁵⁾	f _{VCO} = 100 MHz, Pdiv = 1		45%	55%	
I ² C PARAMETER						
V _{IK}	SCL and SDA input clamp voltage	V _{DD} = 1.7 V, I _I = - 18 mA			- 1.2	V
I _{IH}	SCL and SDA input current	V _I = V _{DD} , V _{DD} = 1.9 V			±10	μA
V _{IH}	I ² C input high voltage ⁽⁶⁾		0.7 × V _{DD}			V
V _{IL}	I ² C input low voltage ⁽⁶⁾			0.3 × V _{DD}		V
V _{OL}	SDA low-level output voltage	I _{OL} = 3 mA, V _{DD} = 1.7 V			0.2 × V _{DD}	V

over recommended operating free-air temperature range (unless otherwise noted)

	TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
C _I	SCL-SDA input capacitance V _I = 0 V or V _{DD}		3	10	pF
EEPROM SPECIFICATION					
EEcyc	Programming cycles of EEPROM	100	1000		cycles
EEret	Data retention	10			years

- (1) All typical values are at respective nominal V_{DD}.
 (2) Jitter depends on configuration. Jitter data is for input frequency = 27 MHz, f_{VCO} = 108 MHz, f_{OUT} = 27 MHz (measured at Y2).
 (3) Y1 supplied by PLL1 and configured to same frequency as Y2.
 (4) The tsk(o) specification is only valid for equal loading of each bank of outputs, and the outputs are generated from the same divider.
 (5) odc depends on the output rise and fall time (t_r and t_f); data sampled on the rising edge (t_r)
 (6) SDA and SCL pins are 3.3-V tolerant.

6.6 Timing Requirements

over recommended ranges of supply voltage, load, and operating free-air temperature

			MIN	NOM	MAX	UNIT
CLK_IN						
f _{CLK}	LVCMOS clock input frequency	PLL bypass mode	0		160	MHz
		PLL mode	8		160	
t _r and t _f	Rise and fall time, CLK signal (20% to 80%)				3	ns
	Duty cycle of CLK at V _{DD} / 2		40%		60%	
I²C (SEE 图 8-8)						
f _{SCL}	SCL clock frequency	Standard mode	0		100	kHz
		Fast mode	0		400	
t _{su} (START)	START setup time (SCL high before SDA low)	Standard mode	4.7			μs
		Fast mode	0.6			
t _h (START)	START hold time (SCL low after SDA low)	Standard mode	4			μs
		Fast mode	0.6			
t _w (SCLL)	SCL low-pulse duration	Standard mode	4.7			μs
		Fast mode	1.3			
t _w (SCLH)	SCL high-pulse duration	Standard mode	4			μs
		Fast mode	0.6			
t _h (SDA)	SDA hold time (SDA valid after SCL low)	Standard mode	0		3.45	μs
		Fast mode	0		0.9	
t _{su} (SDA)	SDA setup time	Standard mode	250			ns
		Fast mode	100			
t _r	SCL-SDA input rise time	Standard mode			1000	ns
		Fast mode			300	
t _f	SCL-SDA input fall time				300	ns
t _{su} (STOP)	STOP setup time	Standard mode	4			μs
		Fast mode	0.6			
t _{BUS}	Bus free time between a STOP and START condition	Standard mode	4.7			μs
		Fast mode	1.3			

6.7 Typical Characteristics

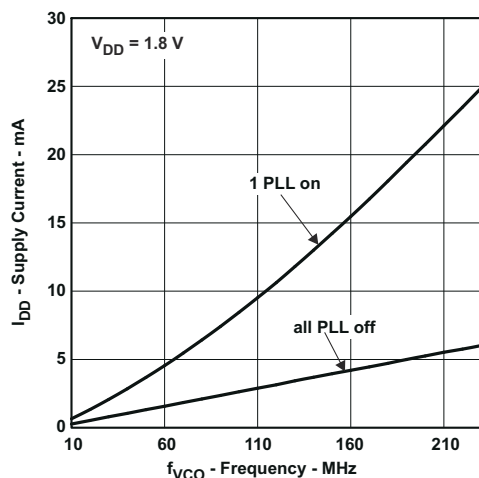


图 6-1. CDCE913-Q1 or CDCEL913-Q1 Supply Current vs PLL Frequency

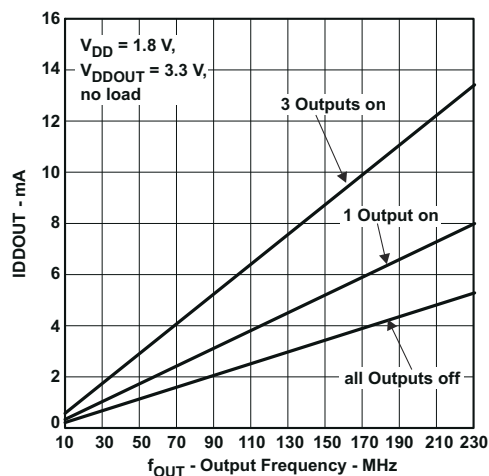


图 6-2. CDCE913-Q1 Output Current vs Output Frequency

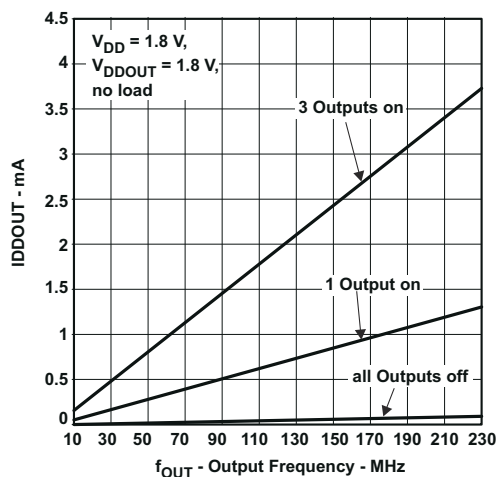


图 6-3. CDCEL913-Q1 Output Current vs Output Frequency

7 Parameter Measurement Information

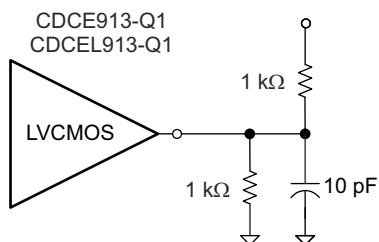


图 7-1. Test Load

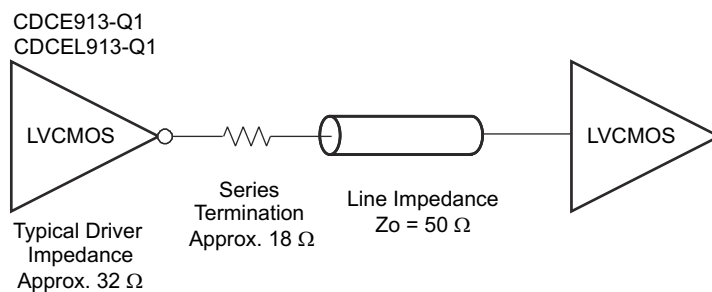


图 7-2. Test Load for 50-Ω Board Environment

8 Detailed Description

8.1 Overview

The CDCE913-Q1 and CDCEL913-Q1 devices are modular PLL-based, low-cost, high-performance, programmable clock synthesizers, multipliers, and dividers. They generate up to three output clocks from a single input frequency. Each output can be programmed in-system for any clock frequency up to 230 MHz, using the integrated configurable PLL.

The CDCE913-Q1 and CDCEL913-Q1 devices have separate output supply pins, V_{DDOUT} , with output of 1.8 V for the CDCEL913-Q1 device and 2.5 V to 3.3 V for the CDCE913-Q1 device. Additionally, each device requires a 1.8-V supply applied to the VDD pin for the device to operate.

The input accepts an external crystal or LVCMOS clock signal. If an external crystal is used, an on-chip load capacitor is adequate for most applications. The value of the load capacitor is programmable from 0 pF to 20 pF. Additionally, a selectable on-chip VCXO allows synchronization of the output frequency to an external control signal, that is, the PWM signal.

The deep M / N divider ratio allows the generation of zero-ppm audio-video, networking (WLAN, Bluetooth, Ethernet, GPS) or interface (USB, IEEE1394, memory stick) clocks from, for example, a 27-MHz reference input frequency.

The PLL supports spread-spectrum clocking (SSC). SSC can be center-spread or down-spread clocking, which is a common technique to reduce electromagnetic interference (EMI).

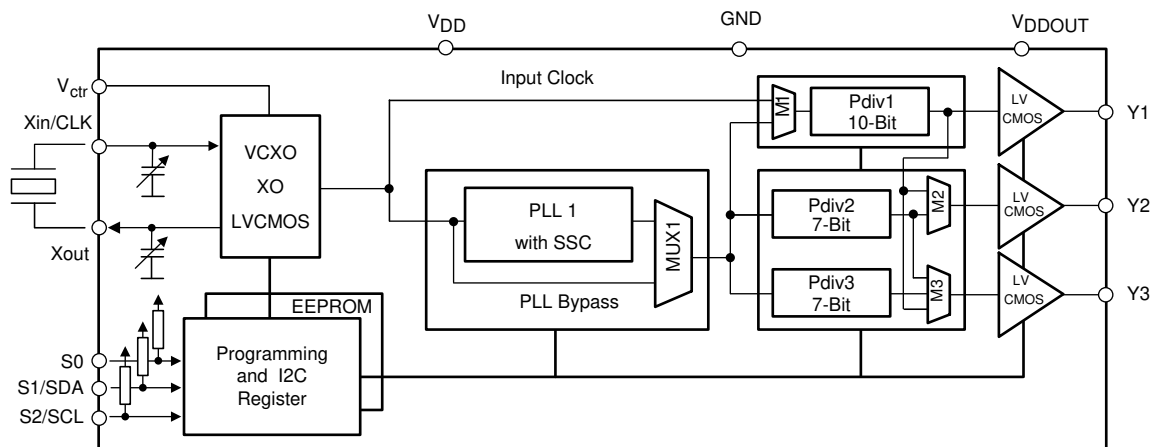
Based on the PLL frequency and the divider settings, the internal loop filter components are automatically adjusted to achieve high stability and optimized jitter transfer characteristics.

The device supports nonvolatile EEPROM programming for easy customization of the device to the application. The device is preset to a factory default configuration (see [Default Device Configuration](#)) that can be reprogrammed to a different application configuration before PCB assembly, or reprogrammed by in-system programming. All device settings are programmable through the SDA-SCL bus, a 2-wire serial interface.

Three programmable control inputs, S0, S1, and S2, can be used to select different frequencies, change SSC setting for lowering EMI, or control other features such as outputs disabled to low, outputs in Hi-Z state, power down, PLL bypass, and so forth).

The CDCE913-Q1 device operates in a temperature range of -40°C to $+125^{\circ}\text{C}$, and the CDCEL913-Q1 device operates in a temperature range of -40°C to 85°C .

8.2 Functional Block Diagram



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8.3 Feature Description

8.3.1 Control Terminal Configuration

The CDCE913-Q1 and CDCEL913-Q1 devices have three user-definable control terminals (S0, S1, and S2), which allow external control of device settings. They can be programmed to any of the following functions:

- Spread-spectrum clocking selection → spread type and spread amount selection
- Frequency selection → switching between any of two user-defined frequencies
- Output state selection → output configuration and power-down control

The user can predefine up to eight different control settings. 表 8-1 and 表 8-2 explain these settings.

表 8-1. Control Terminal Definition

EXTERNAL CONTROL BITS	PLL1 SETTING			Y1 SETTING
Control function	PLL frequency selection	SSC selection	Output Y2 and Y3 selection	Output Y1 and power-down selection

表 8-2. PLLx Setting
(Can Be Selected for Each PLL Individually)⁽¹⁾

SSCx [3 Bits]			CENTER	DOWN
SSC SELECTION (CENTER AND DOWN)				
0	0	0	0% (off)	0% (off)
0	0	1	±0.25%	– 0.25%
0	1	0	±0.5%	– 0.5%
0	1	1	±0.75%	– 0.75%
1	0	0	±1.0%	– 1.0%
1	0	1	±1.25%	– 1.25%
1	1	0	±1.5%	– 1.5%
1	1	1	±2.0%	– 2.0%

- (1) Center and down-spread, Frequency0, Frequency1, State0, and State1 are user-definable in PLLx configuration register.

表 8-3. PLLx Setting, Frequency Selection (Can Be Selected for Each PLL Individually)⁽¹⁾

FSx	FUNCTION
0	Frequency0
1	Frequency1

- (1) Frequency0 and Frequency1 can be any frequency within the specified f_{VCO} range.

表 8-4. PLLx Setting, Output Selection (Y2, Y3)⁽¹⁾

Y2, Y3	FUNCTION
0	State0
1	State1

- (1) State0 or State1 selection is valid for both outputs of the corresponding PLL module and can be power down, Hi-Z state, low, or active.

表 8-5. Y1 Setting⁽¹⁾

Y1	FUNCTION
0	State 0
1	State 1

- (1) State0 and State1 are user-definable in the generic configuration register and can be power down, Hi-Z state, low, or active.

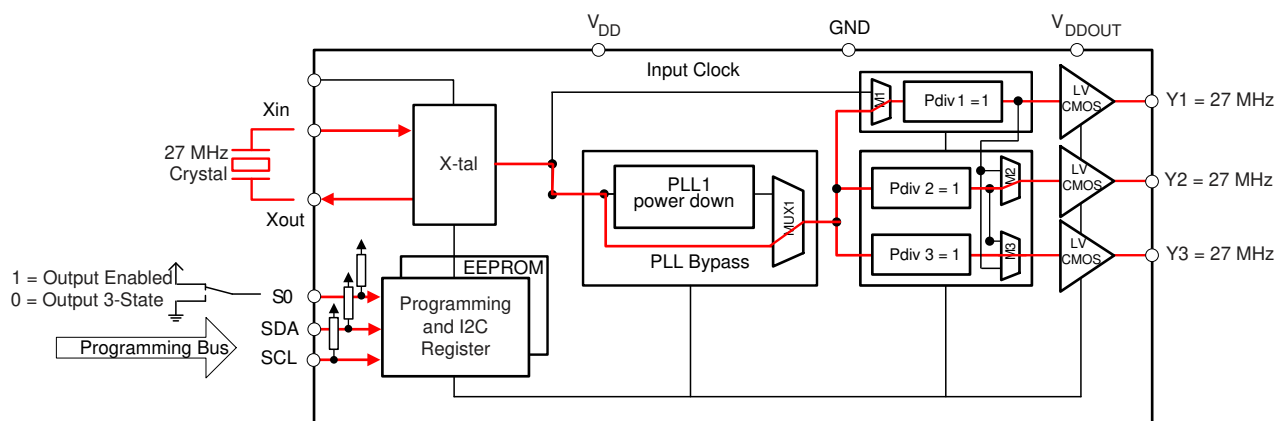
The S1/SDA and S2/SCL pins of the CDCE913-Q1 and CDCEL913-Q1 devices are dual-function pins. In the default configuration, they are defined as SDA and SCL for the serial programming interface. They can be programmed as control pins (S1 and S2) by setting the appropriate bits in the EEPROM. Changes to the control register (Bit [6] of byte *02h*) have no effect until they are written into the EEPROM.

When they are set as control pins, the serial programming interface is no longer available. However, if V_{DDOUT} is forced to GND, the two control pins, S1 and S2, temporally act as serial programming pins (SDA and SCL).

S0 is *not* a multi-use pin; it is a control pin only.

8.3.2 Default Device Configuration

The internal EEPROM of the CDCE913-Q1 and CDCE913-Q1 devices is preconfigured with a factory default configuration, as shown in [Figure 8-1](#). The input frequency is passed through the output as a default, thus allowing the device to operate in default mode without the extra production step of programming it. The default setting appears after power is supplied or after a power-down – power-up sequence until the device is reprogrammed by the user to a different application configuration. A new register setting is programmed through the serial I²C interface.



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图 8-1. Default Configuration

表 8-6 shows the factory default setting for the Control Terminal register. While eight different register settings are possible, in the default configuration, only the first two settings (0 and 1) can be selected with S0, as S1 and S2 are configured as programming pins in default mode.

表 8-6. Factory Default Setting for Control Terminal Register⁽¹⁾

			Y1	PLL1 SETTINGS		
EXTERNAL CONTROL PINS			OUTPUT SELECTION	FREQUENCY SELECTION	SSC SELECTION	OUTPUT SELECTION
S2	S1	S0	Y1	FS1	SSC1	Y2Y3
SCL (I ² C)	SDA (I ² C)	0	3-state	f _{VCO1_0}	Off	Hi-Z state

表 8-6. Factory Default Setting for Control Terminal Register⁽¹⁾ (续)

EXTERNAL CONTROL PINS			Y1	PLL1 SETTINGS		
			OUTPUT SELECTION	FREQUENCY SELECTION	SSC SELECTION	OUTPUT SELECTION
SCL (I ² C)	SDA (I ² C)	1	Enabled	f _{VCO1_0}	Off	Enabled

(1) In default mode or when programmed respectively, S1 and S2 act as serial programming interface, I²C. They do not have any control-pin function but they are internally interpreted as if S1 = 0 and S2 = 0. However, S0 is a control pin, which in the default mode switches all outputs ON or OFF (as previously predefined).

8.3.3 I²C Serial Interface

The CDCE913-Q1 and CDCEL913-Q1 devices operate as a target device on the 2-wire serial I²C bus, compatible with the popular SMBus or I²C specification. The devices operate in the standard-mode transfer (up to 100 kbps) and fast-mode transfer (up to 400 kbps), and supports 7-bit addressing.

The S1/SDA and S2/SCL pins of the CDCE913-Q1 and CDCEL913-Q1 devices are dual-function pins. In the default configuration, the pins are used as the I²C serial programming interface. The pins can be reprogrammed as general-purpose control pins, S1 and S2, by changing the corresponding EEPROM setting, byte 02h, bit [6].

8.3.4 Data Protocol

The device supports *Byte Write and Byte Read* and *Block Write and Block Read* operations.

For *Byte Write/Read* operations, the system controller can individually access addressed bytes.

For *Block Write/Read* operations, the bytes are accessed in sequential order from lowest to highest byte (with most-significant bit first) with the ability to stop after any complete byte has been transferred. The numbers of bytes read out are defined by the byte count in the generic configuration register. At the *Block Read* instruction, all bytes defined in byte count must be read out to finish the read cycle correctly.

When a byte has been sent, the byte is written into the internal register and is effective immediately. This applies to each transferred byte, regardless of whether this is a *Byte Write* or a *Block Write* sequence.

If the EEPROM write cycle is initiated, the internal registers are written into the EEPROM. Data can be read out during the programming sequence (*Byte Read* or *Block Read*). The programming status can be monitored by *EEPIP*, byte 01h – bit 6. Before beginning EEPROM programming, pull CLKIN LOW. CLKIN must be held LOW for the duration of EEPROM programming. After initiating EEPROM programming with *EEWRITE*, byte 06h-bit 0, do not write to the device registers until *EEPIP* is read back as a 0.

The offset of the indexed byte is encoded in the command code, as described in 表 8-8.

表 8-7. Target Receiver Address (7 Bits)

DEVICE	A6	A5	A4	A3	A2	A1 ⁽¹⁾	A0 ⁽¹⁾	R/W
CDCE913-Q1 and CDCEL913-Q1	1	1	0	0	1	0	1	1/0
CDCEx925	1	1	0	0	1	0	0	1/0
CDCEx937	1	1	0	1	1	0	1	1/0
CDCEx949	1	1	0	1	1	0	0	1/0

(1) Address bits A0 and A1 are programmable through the I²C bus (byte 01, bits [1:0]). This allows addressing up to 4 devices connected to the same I²C bus. The least-significant bit of the address byte designates a write or read operation.

8.4 Device Functional Modes

8.4.1 SDA and SCL Hardware Interface

图 8-2 shows how the CDCE913-Q1 and CDCEL913-Q1 clock synthesizer is connected to the I²C serial interface bus. Multiple devices can be connected to the bus, but it may be necessary to reduce the speed (400 kHz is the maximum) if many devices are connected.

The pullup resistors (R_P) depend on the supply voltage, bus capacitance, and number of connected devices. The recommended pullup value is 4.7 k Ω . The resistor must meet the minimum sink current of 3 mA at $V_{OLmax} = 0.4$ V for the output stages (for more details see the SMBus or I²C bus specification).

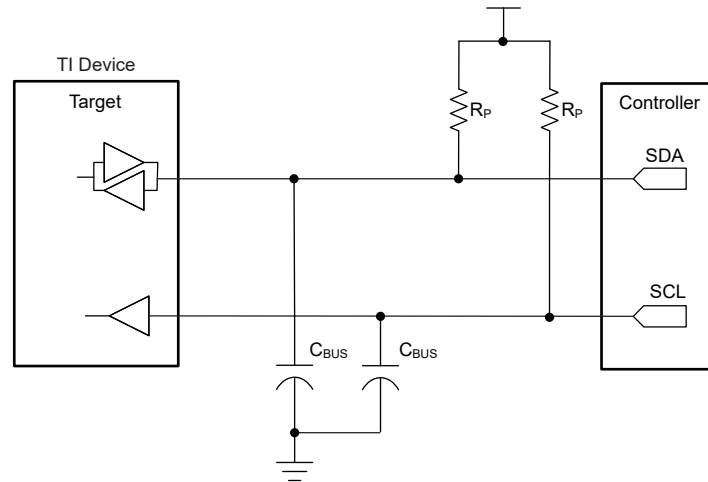


图 8-2. I²C Hardware Interface

8.5 Programming

表 8-8. Command Code Definition

BIT	DESCRIPTION
7	0 = Block Read or Block Write operation 1 = Byte Read or Byte Write operation
(6:0)	Byte offset for Byte Read, Block Read, Byte Write, and Block Write operations

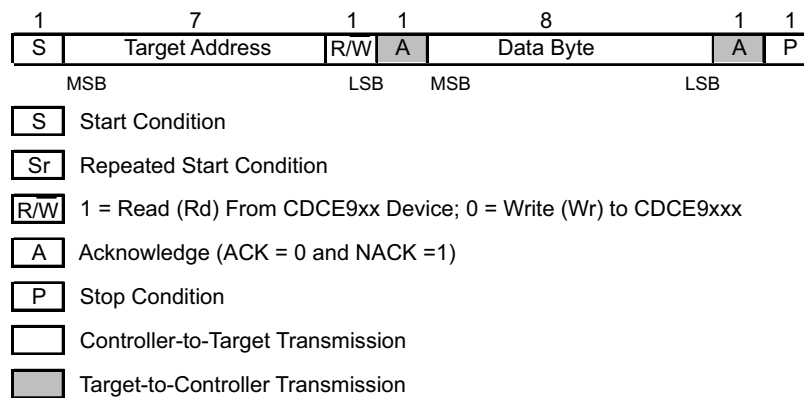


图 8-3. Generic Programming Sequence

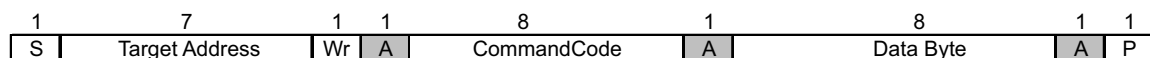


图 8-4. Byte Write Protocol

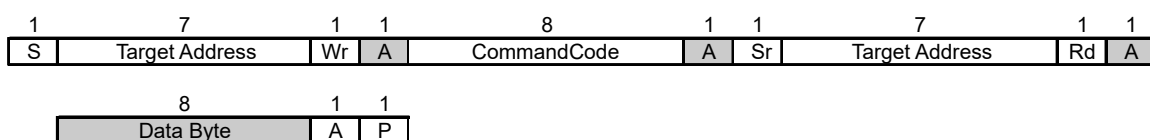
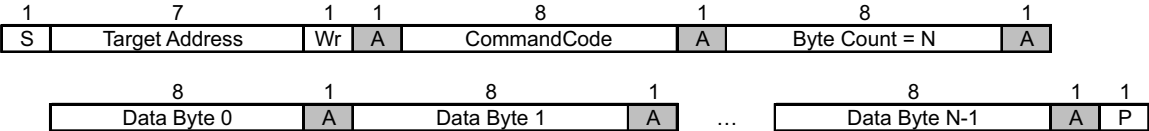


图 8-5. Byte Read Protocol



A. Data byte 0 bits [7:0] is reserved for Revision Code and Vendor Identification. Also, Data byte 0 is used for internal test purpose and must not be overwritten.

图 8-6. Block Write Protocol

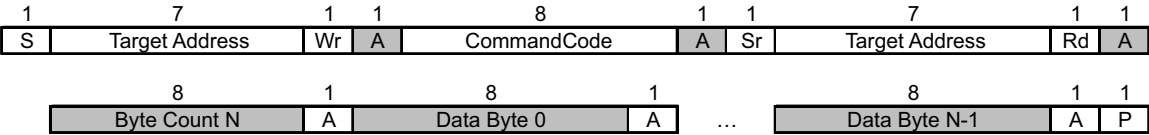


图 8-7. Block Read Protocol

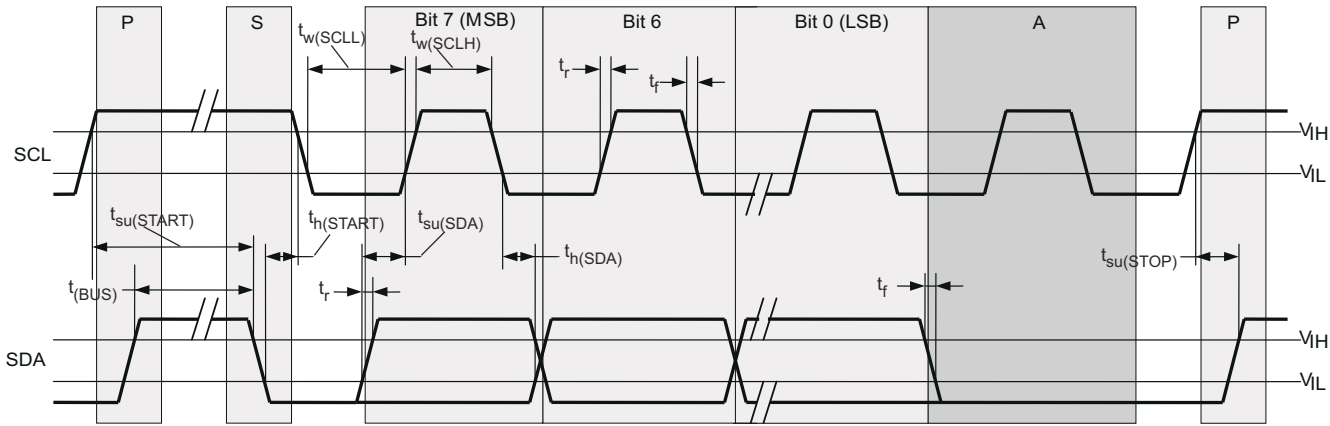


图 8-8. Timing Diagram for I²C Serial Control Interface

9 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

9.1 Application Information

The CDCE913-Q1 device is an easy-to-use, high-performance, programmable CMOS clock synthesizer which can be used as a crystal buffer or clock synthesizer with a separate output supply pin. The CDCE913-Q1 device features an on-chip loop filter and spread-spectrum modulation. Programming can be done through the I²C interface, or previously saved settings can be loaded from on-chip EEPROM. The pins S0, S1, and S2 can be programmed as control pins to select various output settings. This section shows some examples of the CDCE913-Q1 in various applications.

9.2 Typical Application

图 9-1 shows the use of the CDCEL913-Q1 device in an infotainment system, such as in head unit or telematics applications, using a 1.8-V single supply.

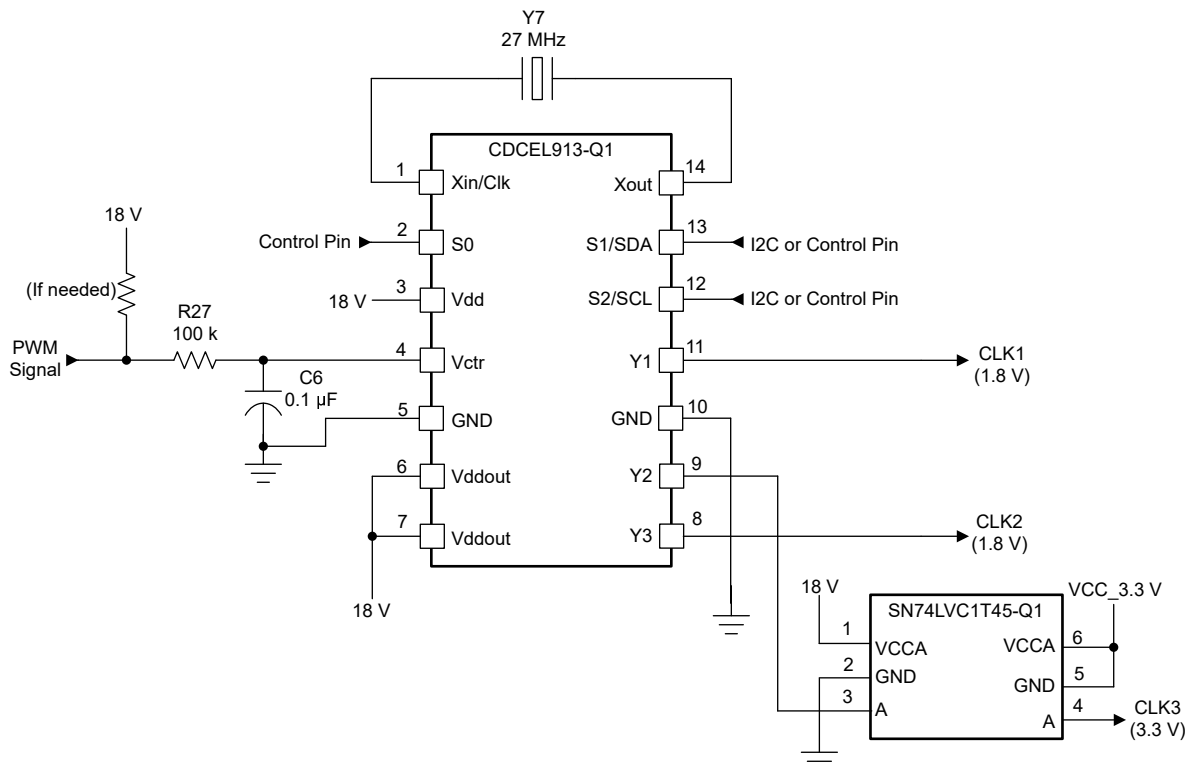


图 9-1. Single-Chip Solution Using a CDCE913-Q1 Device for Generating Clocking Frequencies for Infotainment Application

9.2.1 Design Requirements

The CDCE913-Q1 device supports spread-spectrum clocking (SSC) with multiple control parameters:

- Modulation amount (%)
- Modulation frequency (>20 kHz)
- Modulation shape (triangular, hershey, and others)

- Center spread or down spread ($\pm$ or $-$)

Consider the following sample design requirements:

- EMI ≤ 55 dBmV
- CLK1 frequency = 27 MHz
- CLK2 frequency = 54 MHz
- CLK3 frequency = 108 MHz

For sample calculations of PLL constants, see [PLL Frequency Planning](#).

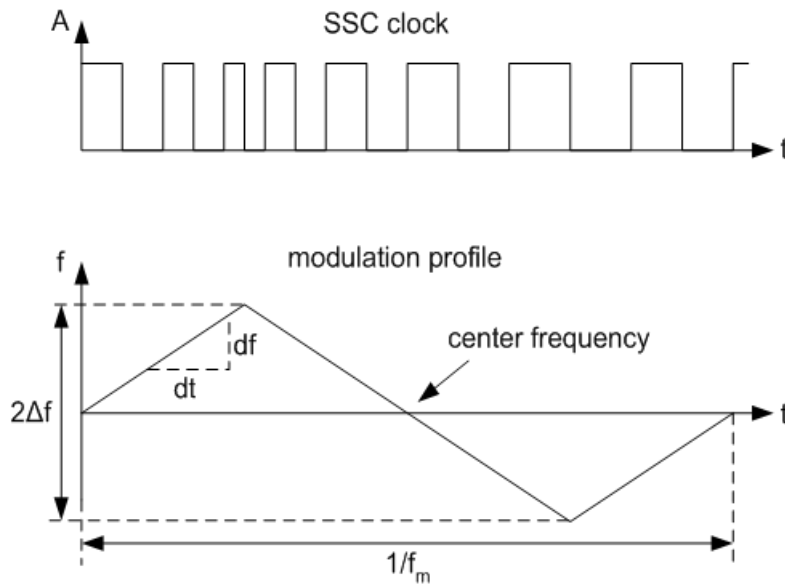


图 9-2. Modulation Frequency (f_m) and Modulation Amount

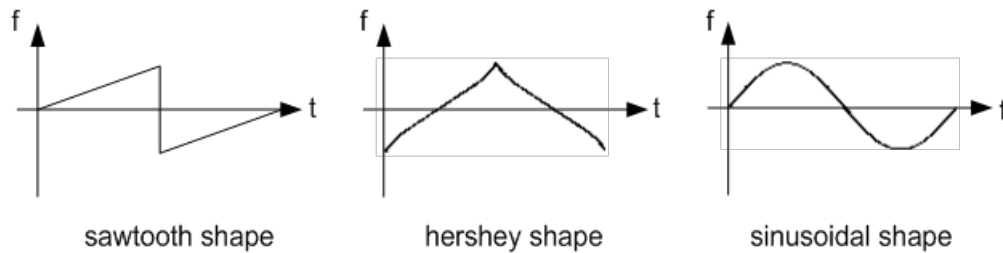
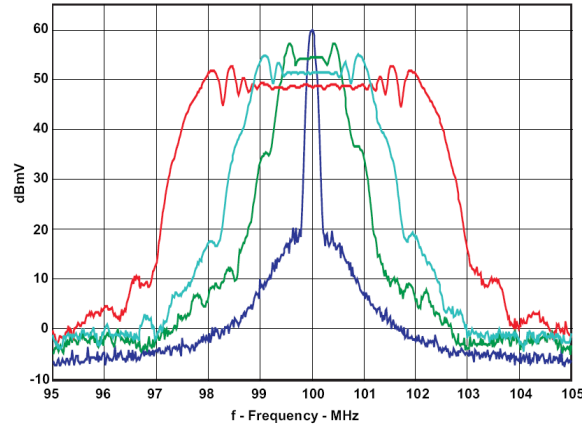


图 9-3. Spread Spectrum Modulation Shapes

9.2.2 Detailed Design Procedure

9.2.2.1 Spread-Spectrum Clock (SSC)

Spread-spectrum modulation is a method to spread emitted energy over a larger bandwidth. In clocking, spread spectrum can reduce electromagnetic interference (EMI) by reducing the level of emission from the clock distribution network.



CDCS502 with a 25-MHz crystal, FS = 1, $f_{OUT} = 100$ MHz, and 0%, ± 0.5 , $\pm 1\%$, and $\pm 2\%$ SSC

图 9-4. Comparison Between Typical Clock Power Spectrum and Spread-Spectrum Clock

Spread-spectrum clocking can be used to help reduce EMI to meet design specifications. For example, a specified EMI threshold of 55 dB/mV would require $\pm 1\%$ spread-spectrum clocking to meet this requirement.

9.2.2.2 PLL Frequency Planning

At a given input frequency (f_{IN}), use [方程式 1](#) to calculate the output frequency (f_{OUT}) of the CDCE913-Q1 or CDCEL913-Q1 device.

$$f_{OUT} = \frac{f_{IN}}{P_{div}} \times \frac{N}{M} \quad (1)$$

where

- M (1 to 511) and N (1 to 4095) are the multiplier or divider values of the PLL
- Pdiv (1 to 127) is the output divider

Use [方程式 2](#) to calculate the target VCO frequency (f_{VCO}) of each PLL.

$$f_{VCO} = f_{IN} \times \frac{N}{M} \quad (2)$$

The PLL internally operates as fractional divider and requires the following multiplier or divider settings:

- N
- $P = 4 - \text{int}(\log_2 N / M)$; if $P < 0$ then $P = 0$
- $Q = \text{int}(N' / M)$
- $R = N' - M \times Q$

where

- $\text{int}(X)$ = integer portion of X
- $N' = N \times 2^P$
- $N \geq M$

$$80 \text{ MHz} \leq f_{VCO} \leq 230 \text{ MHz}$$

$$16 \leq Q \leq 63 \mu s$$

$$0 \leq P \leq 4 \mu s$$

$$0 \leq R \leq 51 \mu s$$

Example:for $f_{IN} = 27$ MHz; $M = 1$; $N = 4$; $Pdiv = 2$

- $f_{OUT} = 54$ MHz
- $f_{VCO} = 108$ MHz
- $P = 4 - \text{int}(\log_2 4) = 4 - 2 = 2$
- $N' = 4 \times 2^2 = 16$
- $Q = \text{int}(16) = 16$
- $R = 16 - 16 = 0$

for $f_{IN} = 27$ MHz; $M = 2$; $N = 11$; $Pdiv = 2$

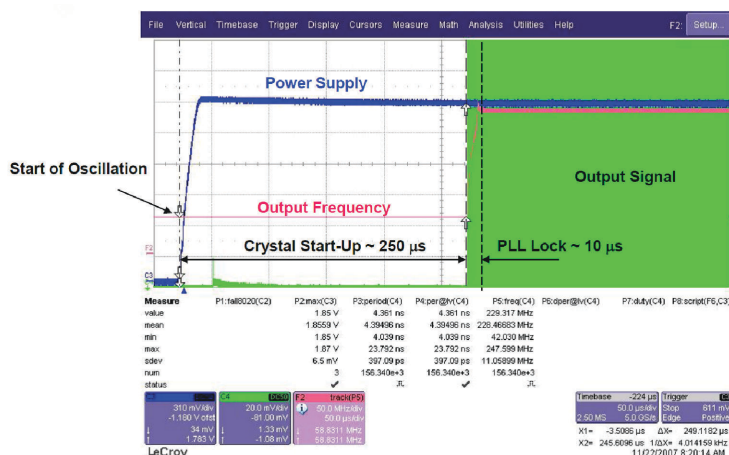
- $f_{OUT} = 74.25$ MHz
- $f_{VCO} = 148.50$ MHz
- $P = 4 - \text{int}(\log_2 5.5) = 4 - 2 = 2$
- $N' = 11 \times 2^2 = 44$
- $Q = \text{int}(22) = 22$
- $R = 44 - 44 = 0$

The values for P, Q, R, and N' are automatically calculated when using TI Pro-Clock™ software.

The frequency of CLK1 shown in the application diagram can be obtained by passing the input frequency of the VCXO directly to output 1. The CLK2 frequency can be achieved by using the PLL constants derived in the first example. The value of CLK3 requires the same PLL constants as CLK2, but Pdiv3 is set to 1 instead of 2 to yield a frequency of 108 MHz.

9.2.2.3 Crystal Oscillator Start-Up

When the CDCE913-Q1 or CDCEL913-Q1 device is used as a crystal buffer, crystal oscillator start-up dominates the start-up time compared to the internal PLL lock time. 图 9-5 shows the oscillator start-up sequence for a 27-MHz crystal input with an 8-pF load. The start-up time for the crystal is on the order of approximately 250 μ s, compared to approximately 10 μ s of lock time. In general, lock time is an order of magnitude less than the crystal start-up time.

**图 9-5. Crystal Oscillator Start-Up vs. PLL Lock Time****9.2.2.4 Frequency Adjustment With Crystal Oscillator Pulling**

The frequency for the CDCE913-Q1 or CDCEL913-Q1 device is adjusted for media and other applications with the VCXO control input V_{ctr} . If a PWM-modulated signal is used as a control signal for the VCXO, an external filter is needed.

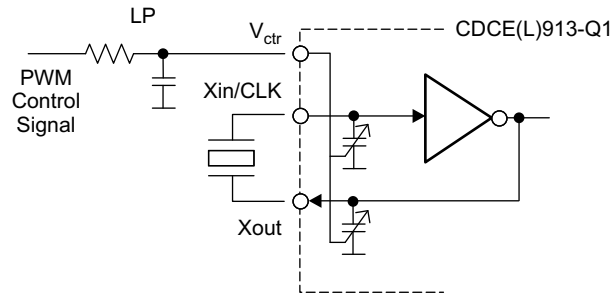


图 9-6. Frequency Adjustment Using PWM Input to the VCXO Control

9.2.2.5 Unused Inputs and Outputs

If VCXO-pulling functionality is not required, V_{ctr} should be left floating. All other unused inputs should be set to GND. Unused outputs should be left floating.

If one output block is not used, TI recommends disabling it. However, TI recommends providing a supply for all output blocks, even if they are disabled.

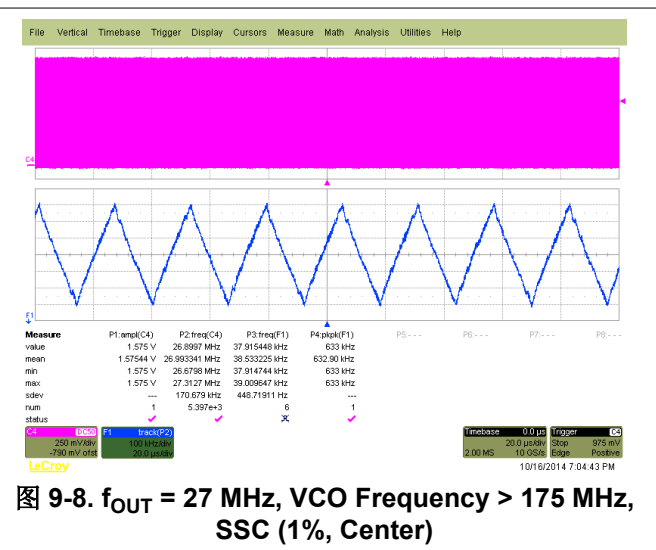
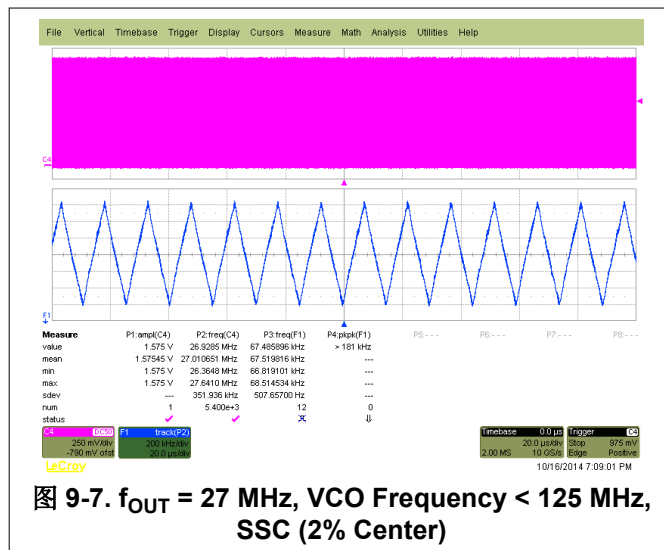
9.2.2.6 Switching Between XO and VCXO Mode

When the CDCE(L)913-Q1 device is in the crystal-oscillator or VCXO configuration, the internal capacitors require different internal capacitance. The following steps are recommended to switch to VCXO mode when the configuration for the on-chip capacitor is still set for XO mode. To center the output frequency to 0 ppm:

1. While in XO mode, put $V_{ctr} = V_{DD} / 2$
2. Switch from XO mode to VCXO mode
3. Program the internal capacitors in order to obtain 0 ppm at the output.

9.2.3 Application Curves

图 9-7, 图 9-8, 图 9-9, and 图 9-10 show CDCE913-Q1 measurements with the SSC feature enabled. Device configuration: 27-MHz input, 27-MHz output.



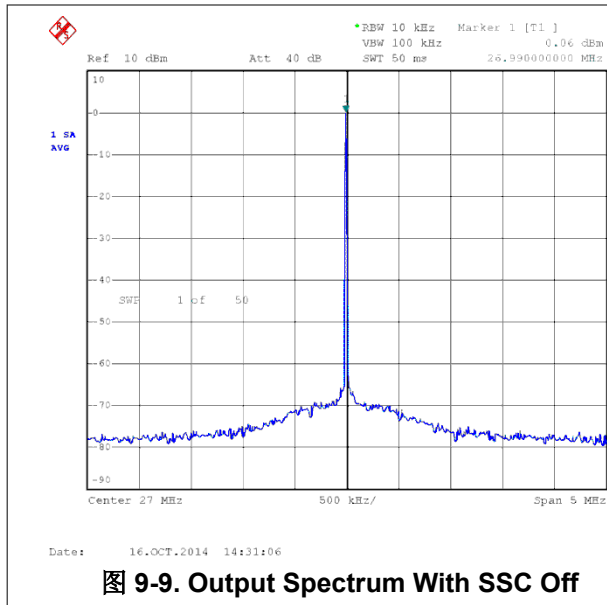


图 9-9. Output Spectrum With SSC Off

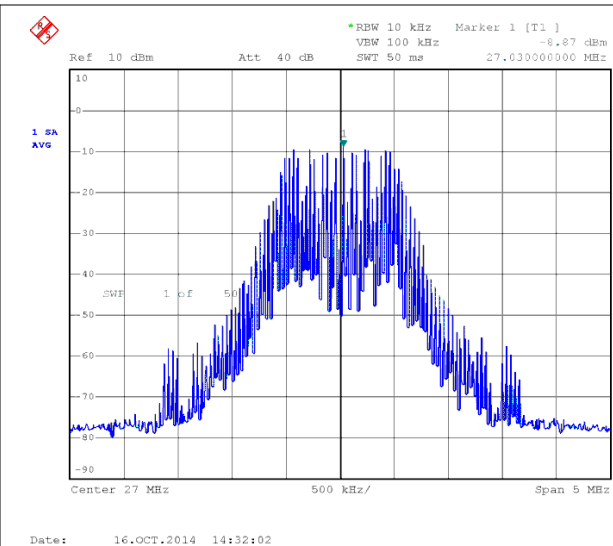


图 9-10. Output Spectrum With SSC On, 2% Center

9.3 Power Supply Recommendations

There is no restriction on the power-up sequence. If V_{DDOUT} is applied first, TI recommends grounding V_{DD} . If V_{DDOUT} is powered while V_{DD} is floating, there is a risk of high current flowing on the V_{DDOUT} pins.

The device has a power-up control that is connected to the 1.8-V supply. This keeps the whole device disabled until the 1.8-V supply reaches a sufficient voltage level. Then, the device switches on all internal components, including the outputs. If a 3.3-V V_{DDOUT} is available before the 1.8-V, the outputs stay disabled until the 1.8-V supply has reached a certain level.

9.4 Layout

9.4.1 Layout Guidelines

When the CDCE913-Q1 device is used as a crystal buffer, any parasitics across the crystal affect the pulling range of the VCXO. Thus, place the crystal units on the board. Crystals should be placed as close to the device as possible, ensuring that the routing lines from the crystal terminals to X_{in} and X_{out} have the same length.

If possible, cut out both ground plane and power plane under the area where the crystal and the routing to the device are placed. In this area, always avoid routing any other signal line, as it could be a source of noise coupling.

Additional discrete capacitors can be required to meet the load capacitance specification of certain crystals. For example, a 10.7-pF load capacitor is not fully programmable on the chip, because the internal capacitor can range from 0 pF to 20 pF with steps of 1 pF. Therefore, the 0.7-pF capacitor can be discretely added on top of an internal 10 pF.

To minimize the inductive influence of the trace, TI recommends placing this small capacitor as close to the device as possible, and symmetrically with respect to X_{in} and X_{out} .

图 9-11 shows a conceptual layout detailing recommended placement of power-supply bypass capacitors. For component-side mounting, use 0402 body-size capacitors to facilitate signal routing. Keep the connections between the bypass capacitors and the power supply on the device as short as possible. Ground the other side of the capacitor using a low-impedance connection to the ground plane.

9.4.2 Layout Example

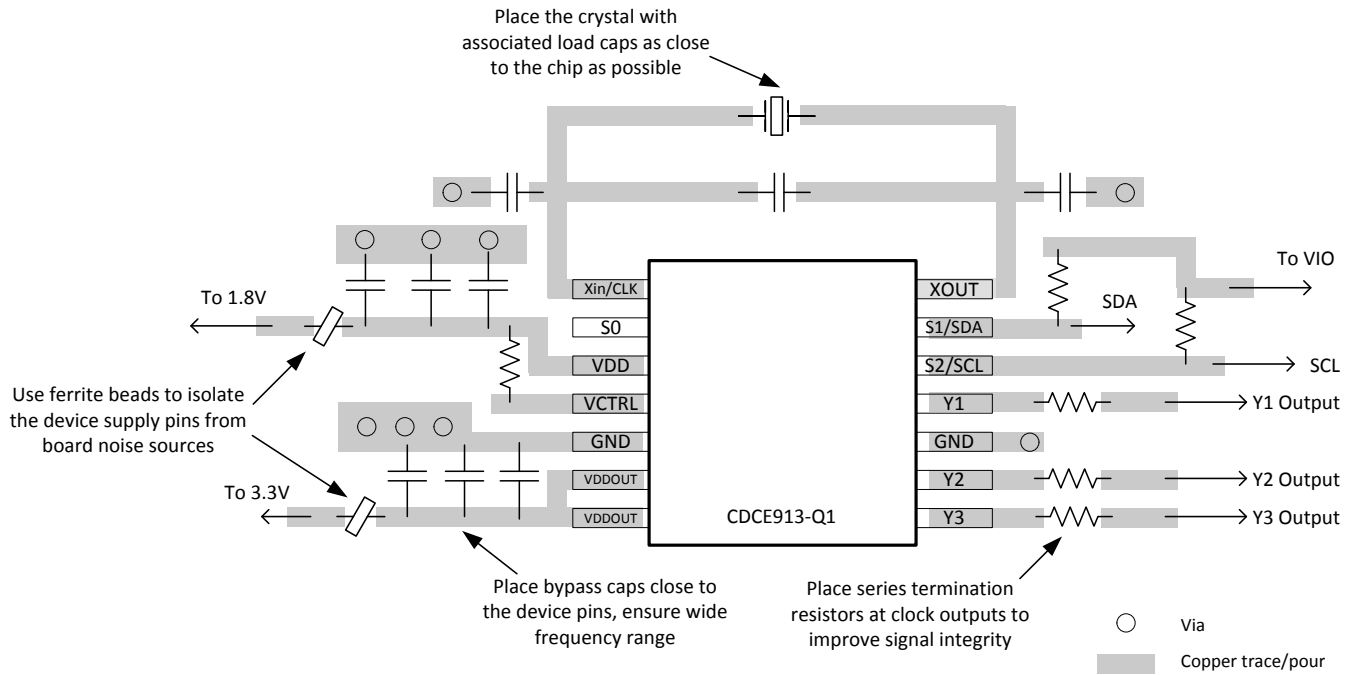


图 9-11. Annotated Layout

10 Register Maps

10.1 I²C Configuration Registers

The clock input, control pins, PLLs, and output stages are user-configurable. The following tables and explanations describe the programmable functions of the CDCE913-Q1 and CDCEL913-Q1 devices. All settings can be manually written into the device through the I²C bus, or programmed by using the TI Pro-Clock™ software. TI Pro-Clock™ software allows the user to make all settings quickly, and automatically calculates the values for optimized performance at lowest jitter.

表 10-1. I²C Registers

ADDRESS OFFSET	REGISTER DESCRIPTION	TABLE
00h	Generic configuration register	表 10-3
10h	PLL1 configuration register	表 10-4

The grey-highlighted bits, described in the configuration register tables in the following pages, belong to the control terminal register. The user can predefine up to eight different control settings. These settings then can be selected by the external control pins, S0, S1, and S2. See the [Control Terminal Configuration](#) section.

表 10-2. Configuration Register, External Control Terminals

				Y1	PLL1 Settings		
EXTERNAL CONTROL PINS				OUTPUT SELECTION	FREQUENCY SELECTION	SSC SELECTION	OUTPUT SELECTION
	S2	S1	S0	Y1	FS1	SSC1	Y2Y3
0	0	0	0	Y1_0	FS1_0	SSC1_0	Y2Y3_0
1	0	0	1	Y1_1	FS1_1	SSC1_1	Y2Y3_1
2	0	1	0	Y1_2	FS1_2	SSC1_2	Y2Y3_2
3	0	1	1	Y1_3	FS1_3	SSC1_3	Y2Y3_3
4	1	0	0	Y1_4	FS1_4	SSC1_4	Y2Y3_4
5	1	0	1	Y1_5	FS1_5	SSC1_5	Y2Y3_5
6	1	1	0	Y1_6	FS1_6	SSC1_6	Y2Y3_6
7	1	1	1	Y1_7	FS1_7	SSC1_7	Y2Y3_7
Address offset ⁽¹⁾				04h	13h	10h – 12h	15h

(1) Address offset refers to the byte address in the configuration register in 表 10-3 and 表 10-4.

表 10-3. Generic Configuration Register

OFFSET ⁽¹⁾	BIT ⁽²⁾	ACRONYM	DEFAULT ⁽³⁾	DESCRIPTION	
00h	7	E_EL	Xb	Device identification (read-only): 1 is CDCE913-Q1 (3.3 V out), 0 is CDCEL913-Q1 (1.8 V out)	
	6:4	RID	Xb	Revision identification number (read-only)	
	3:0	VID	1h	Vendor identification number (read-only)	
01h	7	—	0b	Reserved – always write 0	
	6	EEPIP	0b	EEPROM programming Status: ⁽⁴⁾ (read-only)	0 – EEPROM programming is completed. 1 – EEPROM is in programming mode.
	5	EELOCK	0b	Permanently lock EEPROM data ⁽⁵⁾	0 – EEPROM is not locked. 1 – EEPROM is permanently locked.
	4	PWDN	0b	Device power down (overwrites S0, S1, and S2 settings; configuration register settings are unchanged) Note: PWDN cannot be set to 1 in the EEPROM. 0 – Device active (PLL1 and all outputs are enabled) 1 – Device power down (PLL1 in power down and all outputs in Hi-Z state)	
	3:2	INCLK	00b	Input clock selection:	00 – Xtal 10 – LVCMOS 01 – VCXO 11 – Reserved
	1:0	TARGET_ADDR	01b	Address bits A0 and A1 of the target receiver address	
02h	7	M1	1b	Clock source selection for output Y1:	0 – Input clock 1 – PLL1 clock
	6	SPICON	0b	Operation mode selection for pins 12 and 13 ⁽⁶⁾ 0 – Serial programming interface SDA (pin 13) and SCL (pin 12) 1 – Control pins S1 (pin 13) and S2 (pin 12)	
	5:4	Y1_ST1	11b	Y1-State0/1 definition	
	3:2	Y1_ST0	01b	00 – Device power down (all PLLs in power down and all outputs in Hi-Z state) 01 – Y1 disabled to Hi-Z state	10 – Y1 disabled to low 11 – Y1 enabled
	1:0	Pdiv1 [9:8]	001h	10-bit Y1-output-divider Pdiv1:	0 – Divider reset and stand-by 1 to 1023 – Divider value
03h	7:0	Pdiv1 [7:0]			
04h	7	Y1_7	0b	Y1_x State selection ⁽⁷⁾ 0 – State0 (predefined by Y1_ST0) 1 – State1 (predefined by Y1_ST1)	
	6	Y1_6	0b		
	5	Y1_5	0b		
	4	Y1_4	0b		
	3	Y1_3	0b		
	2	Y1_2	0b		
	1	Y1_1	1b		
	0	Y1_0	0b		
05h	7:3	XCSEL	0Ah	Crystal load capacitor selection ⁽⁸⁾ 00h – 0 pF 01h – 1 pF 02h – 2 pF :14h to 1Fh – 20 pF	
	2:0		0b	Reserved – do not write other than 0	

表 10-3. Generic Configuration Register (续)

OFFSET ⁽¹⁾	BIT ⁽²⁾	ACRONYM	DEFAULT ⁽³⁾	DESCRIPTION
06h	7:1	BCOUNT	20h	7-bit byte count (defines the number of bytes which will be sent from this device at the next <i>Block Read</i> transfer); all bytes must be read out to finish the read cycle correctly.
	0	EEWRITE	0b	Initiate EEPROM write cycle ^{(4) (9)} 0 - No EEPROM write cycle 1 - Start EEPROM write cycle (internal registers are saved to the EEPROM)
07h-0Fh		—	0h	Unused address range

- (1) Writing data beyond 20h may affect device function.
- (2) All data is transferred with the MSB first.
- (3) Unless customer-specific setting
- (4) During EEPROM programming, no data is allowed to be sent to the device through the I²C bus until the programming sequence is completed. However, data can be read out during the programming sequence (*Byte Read* or *Block Read*).
- (5) If this bit is set to high in the EEPROM, the actual data in the EEPROM is permanently locked. No further programming is possible. However, data can still be written through the I²C bus to the internal register to change device function quickly, but new data can no longer be saved to the EEPROM. EELOCK is effective only if written into the EEPROM.
- (6) Selection of *control pins* is effective only if written into the EEPROM. When written into the EEPROM, the serial programming pins are no longer available. However, if V_{DDOUT} is forced to GND, the two control pins, S1 and S2, temporarily act as serial programming pins (SDA-SCL), and the two target receiver address bits are reset to A0 = 0 and A1 = 0.
- (7) These are the bits of the control terminal register (see 表 10-2). The user can predefine up to eight different control settings. These settings then can be selected by the external control pins, S0, S1, and S2.
- (8) The internal load capacitor (C₁, C₂) must be used to achieve the best clock performance. External capacitors should be used only to finely adjust C_L by a few picofarads. The value of C_L can be programmed with a resolution of 1 pF for a crystal load range of 0 pF to 20 pF. For C_L > 20 pF, use additional external capacitors. The device input capacitance value must be considered, which always adds 1.5 pF (6 pF//2 pF) to the selected C_L. For more about VCXO config. and crystal recommendation, see [VCXO Application Guideline for CDCE\(L\)9xx Family](#) (SCAA085).
- (9) The EEPROM WRITE bit must be sent last. This ensures that the content of all internal registers are stored in the EEPROM. The EEWRT cycle is initiated with the rising edge of the EEWRT bit. A static level-high does not trigger an EEPROM WRITE cycle. The EEWRT bit must be reset to low after the programming is completed. The programming status can be monitored by reading out EEPIF. If EELOCK is set to high, no EEPROM programming is possible.

表 10-4. PLL1 Configuration Register

OFFSET ⁽¹⁾	BIT ⁽²⁾	ACRONYM	DEFAULT ⁽³⁾	DESCRIPTION
10h	7:5	SSC1_7 [2:0]	000b	SSC1: PLL1 SSC selection (modulation amount). ⁽⁴⁾ Down 000 (off) 001 - 0.25% 010 - 0.5% 011 - 0.75% 100 - 1.0% 101 - 1.25% 110 - 1.5% 111 - 2.0% Center 000 (off) 001 ± 0.25% 010 ± 0.5% 011 ± 0.75% 100 ± 1.0% 101 ± 1.25% 110 ± 1.5% 111 ± 2.0%
	4:2	SSC1_6 [2:0]	000b	
	1:0	SSC1_5 [2:1]	000b	
11h	7	SSC1_5 [0]		
	6:4	SSC1_4 [2:0]	000b	
	3:1	SSC1_3 [2:0]	000b	
	0	SSC1_2 [2]	000b	
12h	7:6	SSC1_2 [1:0]		
	5:3	SSC1_1 [2:0]	000b	
	2:0	SSC1_0 [2:0]	000b	
13h	7	FS1_7	0b	FS1_x: PLL1 frequency selection ⁽⁴⁾ 0 - f_{VCO1_0} (predefined by PLL1_0 - multiplier/divider value) 1 - f_{VCO1_1} (predefined by PLL1_1 - multiplier/divider value)
	6	FS1_6	0b	
	5	FS1_5	0b	
	4	FS1_4	0b	
	3	FS1_3	0b	
	2	FS1_2	0b	
	1	FS1_1	0b	
	0	FS1_0	0b	

表 10-4. PLL1 Configuration Register (续)

OFFSET ⁽¹⁾	BIT ⁽²⁾	ACRONYM	DEFAULT ⁽³⁾	DESCRIPTION	
14h	7	MUX1	1b	PLL1 multiplexer:	0 - PLL1 1 - PLL1 bypass (PLL1 is in power down)
	6	M2	1b	Output Y2 multiplexer:	0 - Pdiv1 1 - Pdiv2
	5:4	M3	10b	Output Y3 Multiplexer:	00 - Pdiv1-divider 01 - Pdiv2-divider 10 - Pdiv3-divider 11 - Reserved
	3:2	Y2Y3_ST1	11b	Y2, Y3- State0/1definition:	00 - Y2 and Y3 disabled to Hi-Z state (PLL1 is in power down) 01 - Y2 and Y3 disabled to Hi-Z state
	1:0	Y2Y3_ST0	01b		10 - Y2 and Y3 disabled to low 11 - Y2 and Y3 enabled
15h	7	Y2Y3_7	0b	Y2Y3_x output state selection. ⁽⁴⁾ 0 - State0 (predefined by Y2Y3_ST0) 1 - State1 (predefined by Y2Y3_ST1)	
	6	Y2Y3_6	0b		
	5	Y2Y3_5	0b		
	4	Y2Y3_4	0b		
	3	Y2Y3_3	0b		
	2	Y2Y3_2	0b		
	1	Y2Y3_1	1b		
	0	Y2Y3_0	0b		
16h	7	SSC1DC	0b	PLL1 SSC down or center selection:	0 - Down 1 - Center
	6:0	Pdiv2	01h	7-bit Y2-output-divider Pdiv2:	0 - Reset and standby 1 to 127 - Divider value
17h	7	—	0b	Reserved - do not write other than 0	
	6:0	Pdiv3	01h	7-bit Y3-output-divider Pdiv3:	0 - Reset and standby 1 to 127 - Divider value
18h	7:0	PLL1_ON [11:4]	004h	PLL1_0 ⁽⁵⁾ : 30-bit multiplier or divider value for frequency f _{VCO1_0} (for more information, see PLL Frequency Planning).	
19h	7:4	PLL1_ON [3:0]			
	3:0	PLL1_OR [8:5]	000h		
1Ah	7:3	PLL1_OR[4:0]	10h		
	2:0	PLL1_OQ [5:3]			
1Bh	7:5	PLL1_OQ [2:0]	010b	f _{VCO1_0} range selection:	00 - f _{VCO1_0} < 125 MHz 01 - 125 MHz ≤ f _{VCO1_0} < 150 MHz 10 - 150 MHz ≤ f _{VCO1_0} < 175 MHz 11 - f _{VCO1_0} ≥ 175 MHz
	4:2	PLL1_OP [2:0]			
	1:0	VCO1_0_RANGE	00b		
1Ch	7:0	PLL1_1N [11:4]	004h	PLL1_1 ⁽⁵⁾ : 30-bit multiplier or divider value for frequency f _{VCO1_1} (for more information, see PLL Frequency Planning).	
1Dh	7:4	PLL1_1N [3:0]			
	3:0	PLL1_1R [8:5]	000h		
1Eh	7:3	PLL1_1R[4:0]	10h		
	2:0	PLL1_1Q [5:3]			
1Fh	7:5	PLL1_1Q [2:0]	010b	f _{VCO1_1} range selection:	00 - f _{VCO1_1} < 125 MHz 01 - 125 MHz ≤ f _{VCO1_1} < 150 MHz 10 - 150 MHz ≤ f _{VCO1_1} < 175 MHz 11 - f _{VCO1_1} ≥ 175 MHz
	4:2	PLL1_1P [2:0]			
	1:0	VCO1_1_RANGE	00b		

- (1) Writing data beyond 20h may adversely affect device function.
(2) All data is transferred MSB-first.
(3) Unless a custom setting is used
(4) The user can predefine up to eight different control settings. In normal device operation, these settings can be selected by the external control pins, S0, S1, and S2.

(5) PLL settings limits: $16 \leq q \leq 63$, $0 \leq p \leq 7$, $0 \leq r \leq 511$, $0 < N < 4096$

11 器件和文档支持

11.1 文档支持

11.1.1 相关文档

请参阅以下相关文档：

- [使用硅器件替代晶体或晶体振荡器 \(SNAA217\)](#)
- [CDCE\(L\)9xx 和 CDCEx06 编程评估模块 \(SCAU026\)](#)
- [CDCE\(L\)9xx 性能评估模块 \(SCAU022\)](#)
- [针对 CDCE\(L\)9xx 系列的 I²C/EEPROM 常规使用 \(SCAA104\)](#)
- [使用低频字时钟为音频数据转换器生成低相位噪声时钟 \(SCAA088\)](#)
- [针对 CDCE\(L\)9xx 系列选择晶振的实际问题 \(SLEA071\)](#)
- [I²C 在 CDCE\(L\)949、CDCE\(L\)937、CDCE\(L\)925、CDCE\(L\)913 中的应用 \(SCAA105\)](#)
- [面向 CDCE\(L\)9xx 系列的 VCXO 应用指南 \(SCAA085\)](#)

11.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](#) 上的器件产品文件夹。点击 [通知](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

11.3 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

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11.5 静电放电警告



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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

12 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision C (November 2016) to Revision D (February 2024)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• 添加了 CDCE913-Q1 功能安全信息.....	1
• 将提到 I ² C 的旧术语实例通篇更改为控制器和目标。.....	1
• 将器件信息表更改为封装信息.....	1
• Removed the thermal pad from the TSSOP pinout.....	4
• Added Y1 to Y3 cycle-to-cycle jitter and Peak-to-peak period jitter specs with tablenotes explaining the configuration differences.....	6
• Deleted sentence - A different default setting can be programmed upon customer request. Contact Texas Instruments sales or marketing representative for more information.....	13
• Changed units from kbit/s to kbps.....	14
• Added information on allowable data inputs during the EEPROM write cycle in <i>Data Protocol</i>	14

Changes from Revision B (September 2016) to Revision C (November 2016)	Page
• 说明了 CDCEL913-Q1 器件的不同温度范围。.....	1
• Deleted old table notes from the <i>Thermal Information</i> table.	6

Changes from Revision A (June 2013) to Revision B (September 2016)	Page
• 添加了特性说明部分、器件功能模式、应用和实现部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分。.....	1
• Changed ESD Ratings: Human-body model (HBM) from 2500 V to 2000 V and Charged-device model (CDM) from 500 V to 1000 V.....	5
• Changed second S to Sr in <i>Byte Read Protocol</i>	15

Changes from Revision * (June 2013) to Revision A (June 2013)	Page
• 更改了 CDM ESD 分类等级。.....	1
• Added ESD ratings.....	5
• Changed I _{DDPD} typical From: 20 To: 30.....	6
• Changed I _I LVCMOS input current value from typical to maximum.....	6
• Changed I _{IH} LVCMOS input current for S0, S1, and S2 value from typical to maximum.....	6
• Changed I _{IL} LVCMOS input current for S0, S1, and S2 value from typical to maximum.....	6
• Changed <i>Test Load for 50-Ω Board Environment</i>	10
• Changed Output Selection From: (Y2, Y9) To: (Y2, Y3).....	12
• Changed text note for <i>Block Write Protocol</i>	15
• Changed 01h, Bit 7 From: For internal use - always write 1 To: Reserved - always write 0.....	24
• Changed 06h, 7:1 From: 30h To: 20h.....	24

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CDCE913QPWRQ1	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	CE913Q
CDCE913QPWRQ1.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-3-260C-168 HR	-40 to 125	CE913Q
CDCEL913IPWRQ1	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CEL913Q
CDCEL913IPWRQ1.B	Active	Production	TSSOP (PW) 14	2000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	CEL913Q

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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OTHER QUALIFIED VERSIONS OF CDCE913-Q1, CDCEL913-Q1 :

- Catalog : [CDCE913](#), [CDCEL913](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CDCE913QPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
CDCEL913IPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

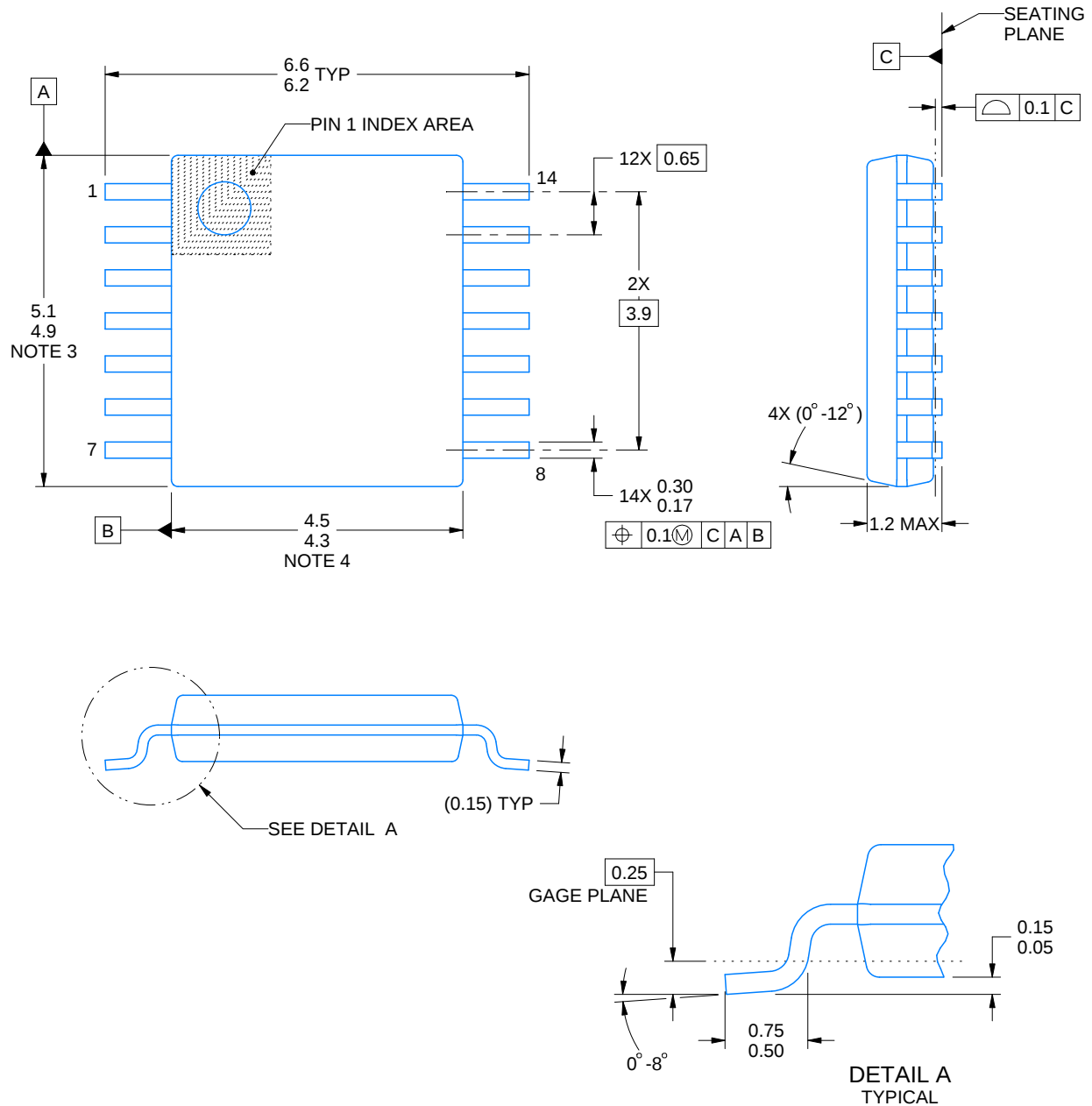
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CDCE913QPWRQ1	TSSOP	PW	14	2000	353.0	353.0	32.0
CDCEL913IPWRQ1	TSSOP	PW	14	2000	353.0	353.0	32.0

PW0014A

PACKAGE OUTLINE

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



4220202/B 12/2023

NOTES:

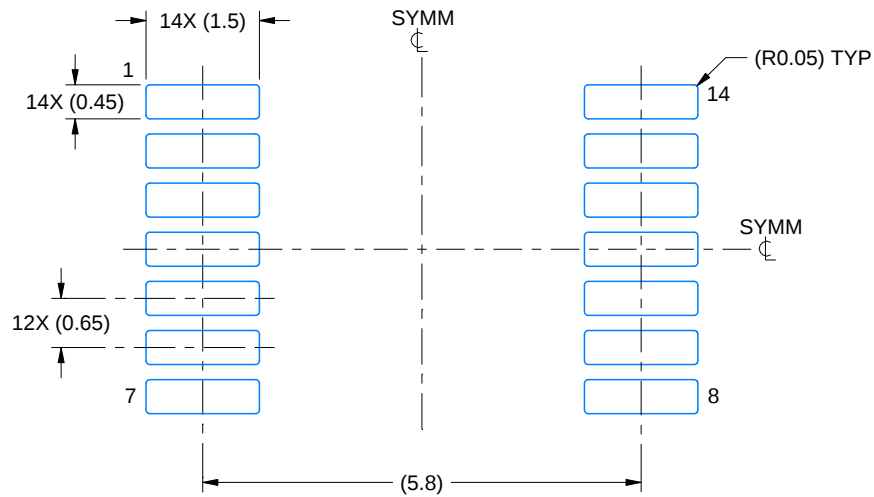
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



SOLDER MASK DETAILS

4220202/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

重要通知和免责声明

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